present invention,

Figs. 17a to 17d are sectional views each schematically showing the process for the surface treatment of the interlayer insulating film in the active matrix substrate in the reflection type liquid crystal display device of the embodiment 2 of the present invention, and

Fig. 18 is a flow chart showing a process for manufacturing the active matrix substrate in the prior art reflection type liquid crystal display device.

[0023]

PREFERRED EMBODIMENTS OF THE INVENTION

Preferred embodiments of the invention will be now described. In accordance with one preferred embodiment of the present invention, a process of making a reflection type liquid crystal display device comprises the steps of:

(a) depositing a metal layer having a low resistance on an insulating substrate(10) to form a source/drain wiring(22,23) by using a first mask;

(b) stacking a silicon layer(30), gate insulating film(40) and gate electrode layer(52) in this order on the insulating substrate(10) having the source/drain wiring formed to form a thin film transistor region and a gate wiring by using a second mask;

(c) depositing a passivation film(61) on the insulating substrate including the source/drain wiring, the thin film transistor region and the gate wiring to form an opening(63) for a transistor, in a predetermined position on the source wiring(22) by using a third mask so that the opening penetrates through the passivation film;